

### Features

- Low On-Resistance:
  - $R_{DS(ON)} < 54m\Omega @ V_{GS} = 10V$
  - $R_{DS(ON)} < 72m\Omega @ V_{GS} = 4.5V$
  - $R_{DS(ON)} < 115m\Omega @ V_{GS} = 2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

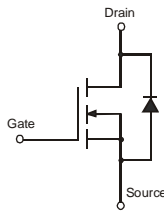
### Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

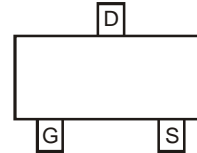
SOT-23



TOP VIEW



EQUIVALENT CIRCUIT



Pin Configuration

### Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 1)	$I_D$	$T_A = 25^\circ C$	3.8
		$T_A = 70^\circ C$	3.1
Drain Current (Note 1)	$I_{DM}$	15	A
Body-Diode Continuous Current (Note 1)	$I_S$	2.0	A

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	1.4	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 1)	$R_{\theta JA}$	90	$^\circ C/W$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ C$

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	800	nA	$V_{DS} = 28V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 80$ $\pm 800$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.62	0.92	1.4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	39 52 90	54 72 115	m $\Omega$	$V_{GS} = 10V, I_D = 3.8A$ $V_{GS} = 4.5V, I_D = 3.6A$ $V_{GS} = 2.5V, I_D = 3.1A$
Forward Transconductance	$ Y_{fs} $	—	3	—	S	$V_{DS} = 5V, I_D = 3.1A$
Source-Drain Diode Forward Voltage	$V_{SD}$	—	—	1.16	V	$V_{GS} = 0V, I_S = 2.0A$
<b>DYNAMIC CHARACTERISTICS</b>						
Gate Resistance	$R_g$	-	4.17	-	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V,$ $f = 1\text{MHz}$
Total Gate Charge (10V)	$Q_g$	-	8.2	-	nC	$V_{GS} = 10V, V_{DS} = 10V,$ $I_D = 3.8A$
Total Gate Charge (4.5V)	$Q_g$	-	3.7	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 3.8A$
Gate-Source Charge	$Q_{gs}$	-	0.7	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	1.1	-	nC	$V_{DD} = 15V, V_{GEN} = 10V,$ $R_{GEN} = 6\Omega, R_L = 3.9\Omega$
Turn-On Delay Time	$t_{D(on)}$	-	1.14	-	ns	
Turn-On Rise Time	$t_r$	-	3.49	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	15.02	-	ns	
Turn-Off Fall Time	$t_f$	-	3.26	-	ns	$V_{DS} = 5V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Input Capacitance	$C_{iss}$	—	305	—	pF	
Output Capacitance	$C_{oss}$	—	74	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	48	—	pF	

- Notes:
1. Device mounted on FR-4 PCB.  $t \leq 5$  sec.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Short duration pulse test used to minimize self-heating effect.

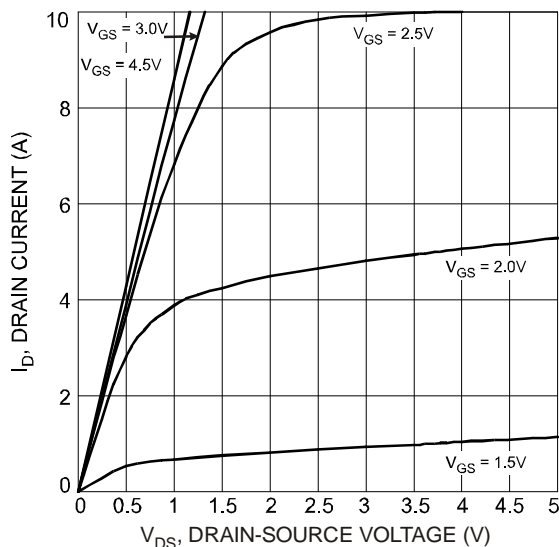


Fig. 1 Typical Output Characteristics

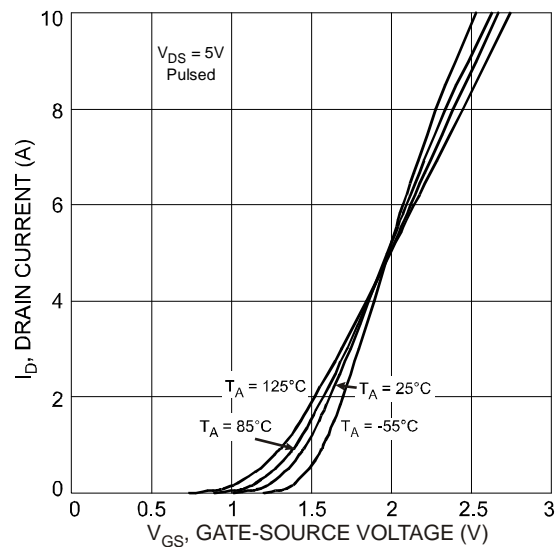


Fig. 2 Typical Transfer Characteristics

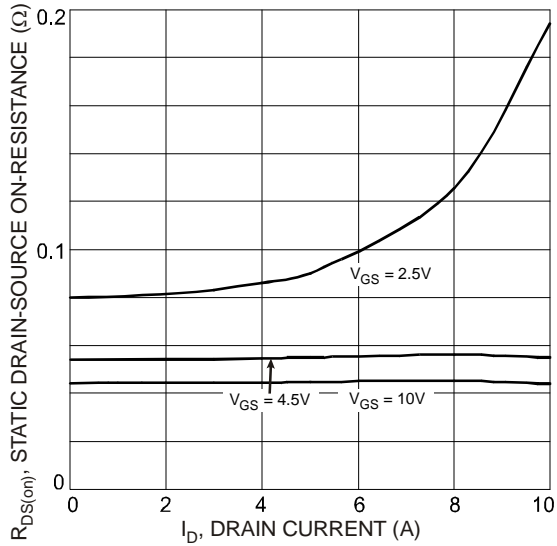


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

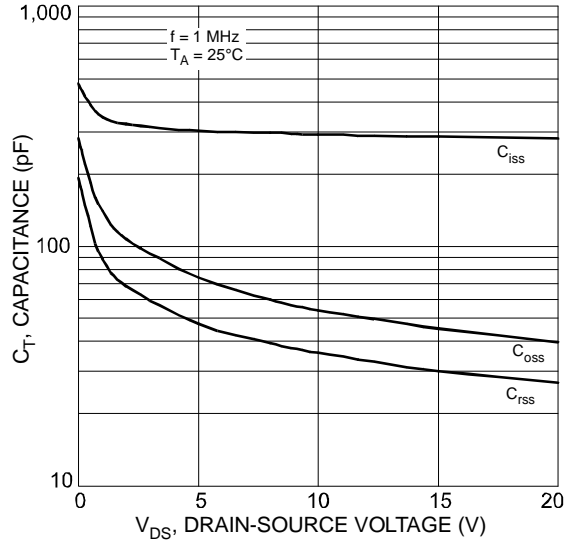


Fig. 4 Typical Total Capacitance

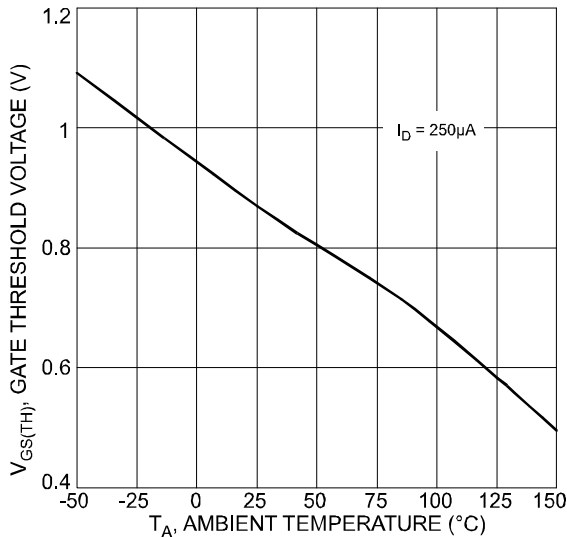


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

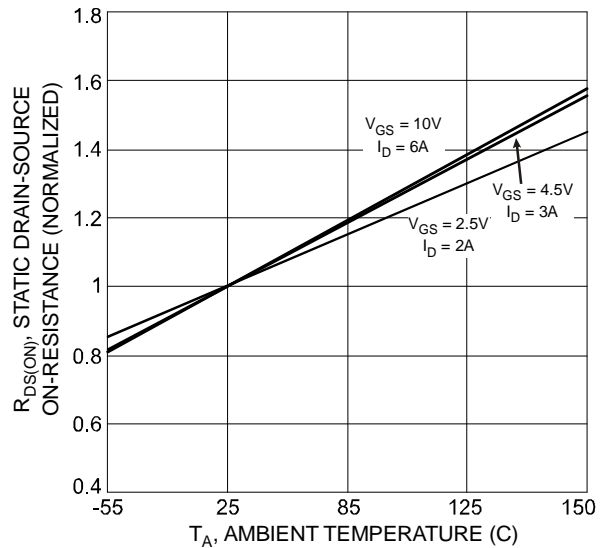


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

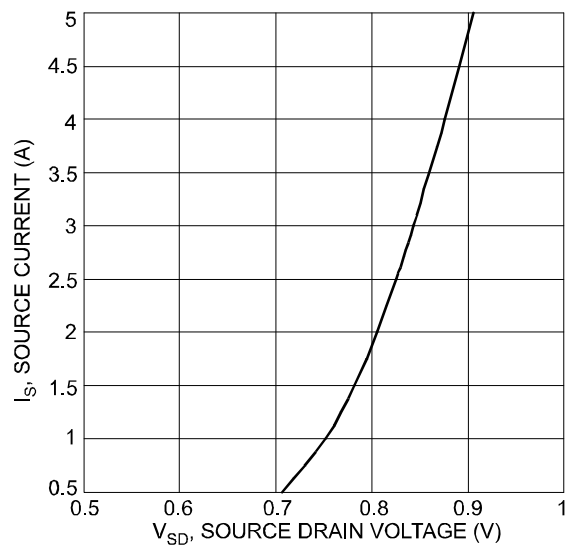


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

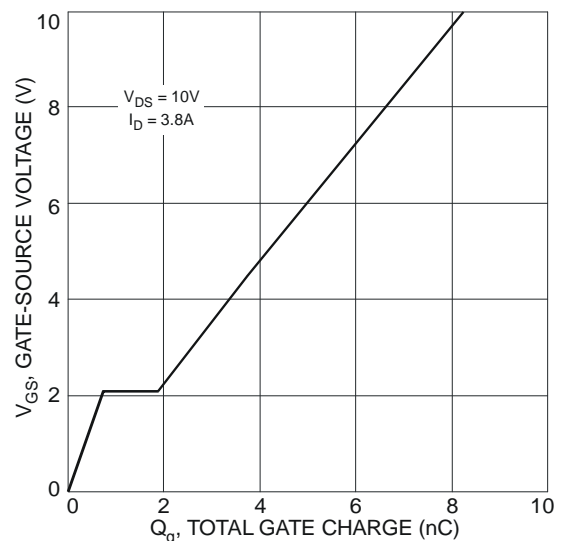


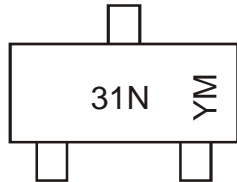
Fig. 8 Gate-Source Voltage vs. Total Gate Charge

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3150L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

### Marking Information



31N = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: T = 2006)  
 M = Month (ex: 9 = September)

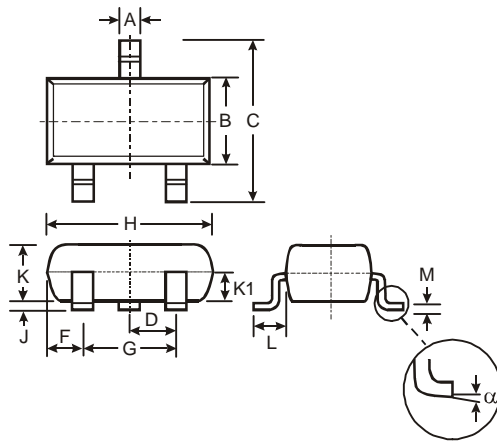
#### Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

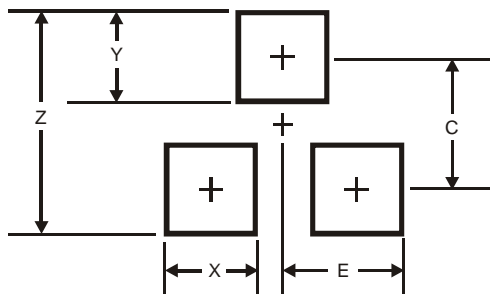
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

### Package Outline Dimensions



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.